NPN Silicon High Voltage Transistor

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Halogen Free. “Green” Device (Note 1)
- AEC-Q101 Qualified
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

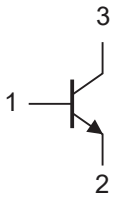
- Operating Junction Temperature Range: -55℃ to +150℃
- Storage Temperature Range: -55℃ to +150℃
- Thermal Resistance: 625℃/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	200	mA
Power Dissipation	P_D	200	mW

Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

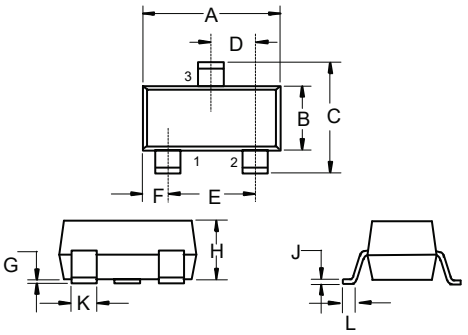
Marking: K3M

Internal Structure



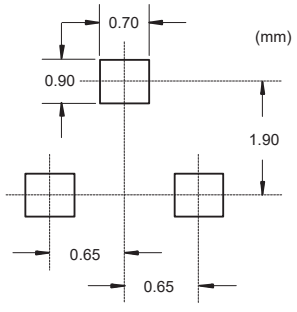
1.BASE
2.EMITTER
3.COLLECTOR

SOT-323



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.083	0.096	2.10	2.45	
D	0.026		0.65		TYP.
E	0.047	0.055	1.20	1.40	
F	0.012	0.016	0.30	0.40	
G	0.000	0.004	0.00	0.10	
H	0.035	0.044	0.90	1.10	
J	0.002	0.010	0.05	0.25	
K	0.006	0.016	0.15	0.40	
L	0.010	0.018	0.26	0.46	

QseecqrcbĀQmjbcpĀN_bĀJ_wmsr



Electrical Characteristics @ T_A=25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	300			V	I_C=100μA, I_E=0
Collector-Emitter Breakdown Voltage*	$V_{(BR)CEO}$	300			V	I_C=1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	I_E=100μA, I_C=0
Collector Cutoff Current	I_{CBO}			0.1	μA	V_{CB}=200V, I_E=0
Emitter Cutoff Current	I_{EBO}			0.1	μA	V_{EB}=6V, I_C=0
DC Current Gain*	$h_{FE(1)}$	25				V_{CE}=10V, I_C=1mA
	$h_{FE(2)}$	40				V_{CE}=10V, I_C=10mA
	$h_{FE(3)}$	40				V_{CE}=10V, I_C=30mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	I_C=20mA, I_B=2mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	I_C=20mA, I_B=2mA
Transition Frequency	f_T	50			MHz	V_{CE}=20V, I_C=10mA, f=100MHz
Collector output Capacitance	C_{cb}			3	pF	V_{CB}=20V, I_E=0,f=1MHz

*.Pulse test: Pulse Width≤300μs,Duty Cycle≤2.0%.

Curve Characteristics

Fig. 1 - Static Characteristics

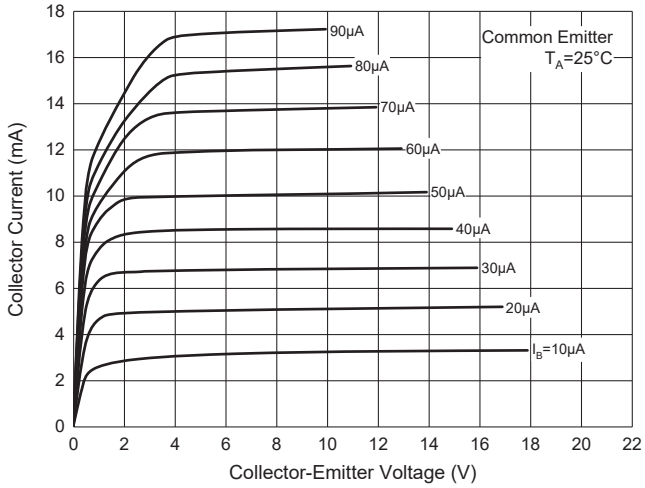


Fig. 2 - DC Current Gain Characteristics

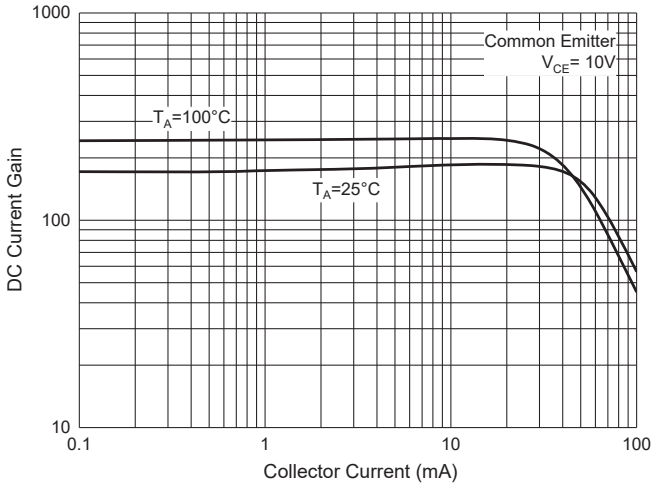


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

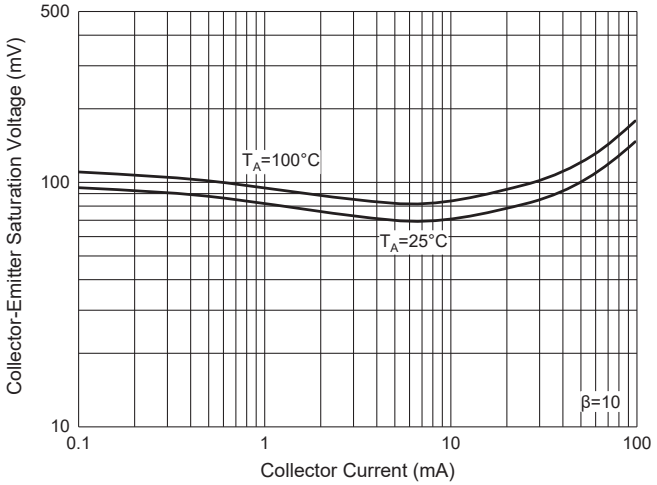


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

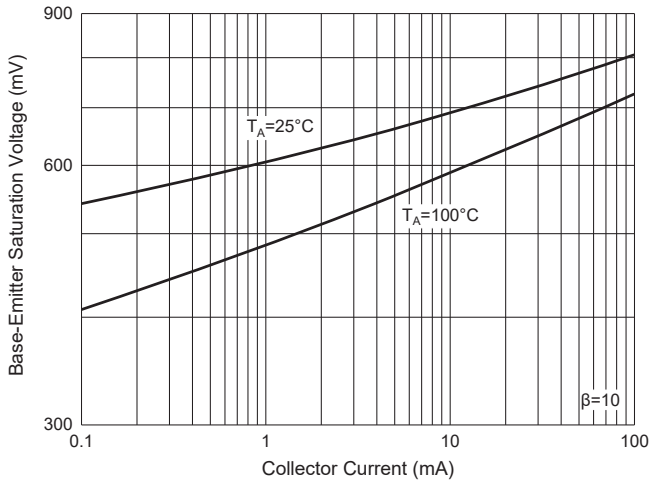


Fig. 5 - Base-Emitter Voltage Characteristics

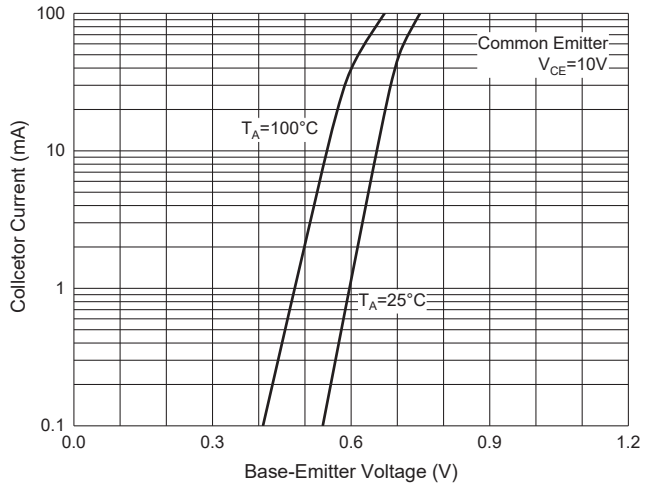
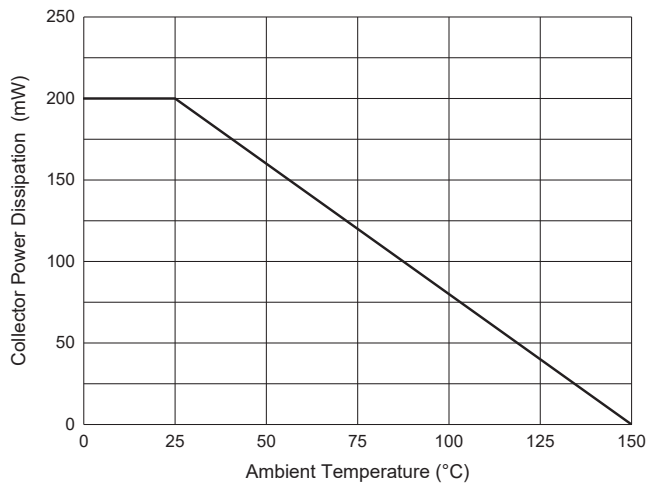


Fig. 6 - Collector Power Derating Curve



Ordering Information

Device	Packing
MMSTA42HE3-TP	Tape&Reel: 3Kpcs/Reel

单击下面可查看定价，库存，交付和生命周期等信息

>>MCC(美微科)